

SEMiX353GD176HDc



SEMiX® 33c

Trench IGBT Modules

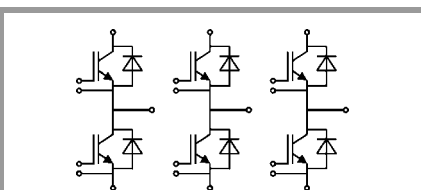
SEMiX353GD176HDc

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders



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Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V_{CES}			1700	V
I_C	$T_j = 150\text{ °C}$	$T_c = 25\text{ °C}$	353	A
		$T_c = 80\text{ °C}$	251	A
I_{Cnom}			225	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$		450	A
V_{GES}			-20 ... 20	V
t_{psc}	$V_{CC} = 1000\text{ V}$	$T_j = 125\text{ °C}$	10	μs
	$V_{GE} \leq 20\text{ V}$			
	$V_{CES} \leq 1700\text{ V}$			
T_j			-55 ... 150	$^{\circ}\text{C}$
Inverse diode				
I_F	$T_j = 150\text{ °C}$	$T_c = 25\text{ °C}$	428	A
		$T_c = 80\text{ °C}$	289	A
I_{Fnom}			225	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$		450	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^{\circ}, T_j = 25\text{ °C}$		1800	A
T_j			-40 ... 150	$^{\circ}\text{C}$
Module				
$I_{t(RMS)}$			600	A
T_{stg}			-40 ... 125	$^{\circ}\text{C}$
V_{isol}	AC sinus 50Hz, $t = 1\text{ min}$		4000	V

Characteristics							
Symbol	Conditions		min.	typ.	max.	Unit	
IGBT							
$V_{CE(sat)}$	$I_C = 225\text{ A}$	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ °C}$	2	2.45	V	
			$T_j = 125\text{ °C}$	2.45	2.9	V	
V_{CE0}			$T_j = 25\text{ °C}$	1	1.2	V	
			$T_j = 125\text{ °C}$	0.9	1.1	V	
r_{CE}	$V_{GE} = 15\text{ V}$			$T_j = 25\text{ °C}$	4.4	5.6	$\text{m}\Omega$
				$T_j = 125\text{ °C}$	6.9	8.0	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 9\text{ mA}$		5.2	5.8	6.4	V	
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1700\text{ V}$			$T_j = 25\text{ °C}$	3		mA
				$T_j = 125\text{ °C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$		$f = 1\text{ MHz}$		19.9		nF
C_{oes}					0.83		nF
C_{res}					0.66		nF
Q_G	$V_{GE} = -8\text{ V...} + 15\text{ V}$				2100	nC	
R_{Gint}	$T_j = 25\text{ °C}$				2.83	Ω	
$t_{d(on)}$	$V_{CC} = 1200\text{ V}$	$I_C = 225\text{ A}$	$T_j = 125\text{ °C}$		250	ns	
t_r			$T_j = 125\text{ °C}$	75	ns		
E_{on}	$R_{Gon} = 5.6\text{ }\Omega$		$T_j = 125\text{ °C}$		155	mJ	
$t_{d(off)}$	$R_{Goff} = 5.6\text{ }\Omega$		$T_j = 125\text{ °C}$		930	ns	
t_f			$T_j = 125\text{ °C}$		180	ns	
E_{off}			$T_j = 125\text{ °C}$		85	mJ	
$R_{th(j-c)}$	per IGBT				0.086	K/W	

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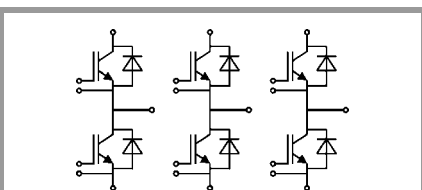
Features

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Typical Applications*

- AC inverter drives
- UPS
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 225\text{ A}$ $V_{GE} = 0\text{ V}$ chip	$T_j = 25\text{ °C}$		1.6	1.75	V
		$T_j = 125\text{ °C}$		1.5	1.7	V
V_{F0}		$T_j = 25\text{ °C}$	0.9	1.1	1.3	V
		$T_j = 125\text{ °C}$	0.7	0.9	1.1	V
r_F		$T_j = 25\text{ °C}$	2.0	2.0	2.0	mΩ
		$T_j = 125\text{ °C}$	2.7	2.7	2.7	mΩ
I_{RRM}	$I_F = 225\text{ A}$	$T_j = 125\text{ °C}$		280		A
Q_{rr}	$di/dt_{off} = 4000\text{ A}/\mu\text{s}$	$T_j = 125\text{ °C}$		83		μC
E_{rr}	$V_{GE} = -15\text{ V}$ $V_{CC} = 1200\text{ V}$	$T_j = 125\text{ °C}$		45		mJ
$R_{th(j-c)}$	per diode				0.13	K/W
Module						
L_{CE}				20		nH
$R_{CC'+EE'}$	res., terminal-chip	$T_C = 25\text{ °C}$		0.7		mΩ
		$T_C = 125\text{ °C}$		1		mΩ
$R_{th(c-s)}$	per module			0.014		K/W
M_s	to heat sink (M5)		3		5	Nm
M_t		to terminals (M6)	2.5		5	Nm
						Nm
w					900	g
Temperatur Sensor						
R_{100}	$T_c = 100\text{ °C}$ ($R_{25} = 5\text{ k}\Omega$)			$493 \pm 5\%$		Ω
$B_{100/125}$	$R_{(T)} = R_{100} \exp[B_{100/125}(1/T - 1/T_{100})]$; $T[\text{K}]$;			$3550 \pm 2\%$		K



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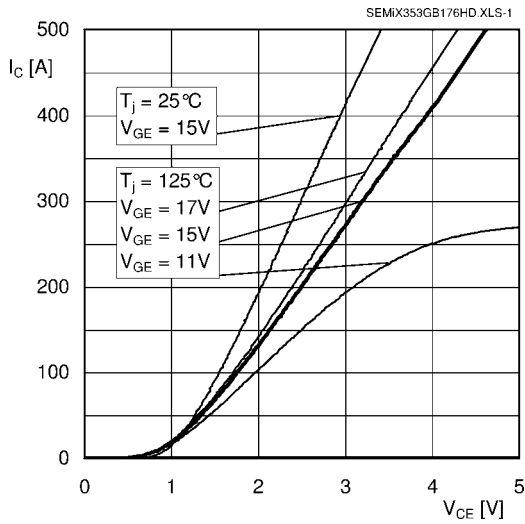


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

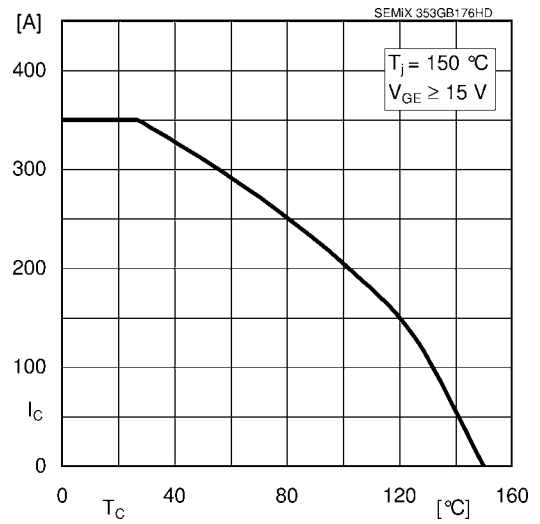


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

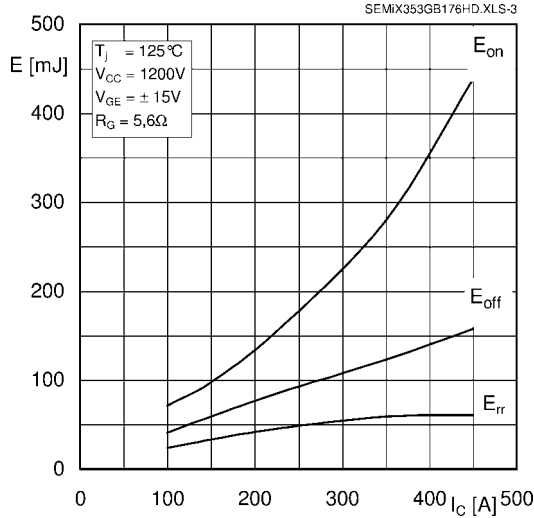


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

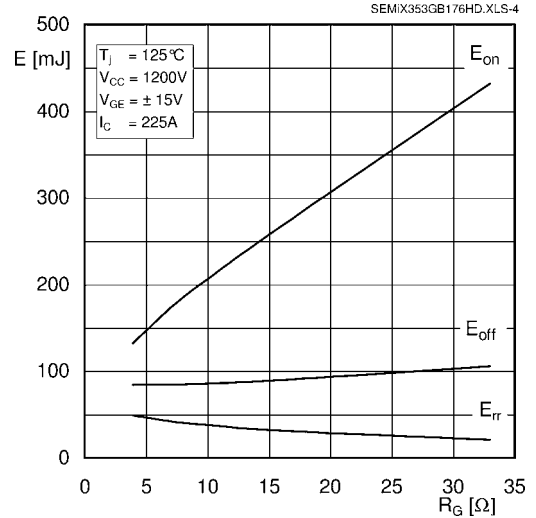


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

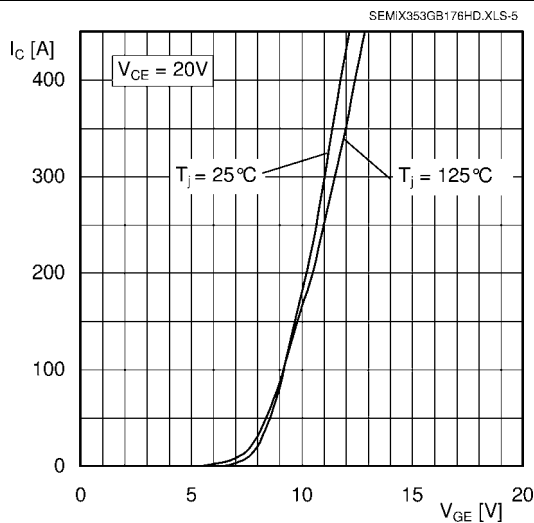


Fig. 5: Typ. transfer characteristic

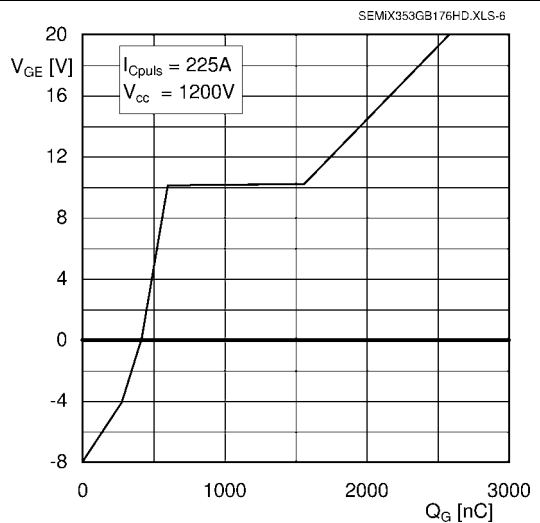


Fig. 6: Typ. gate charge characteristic

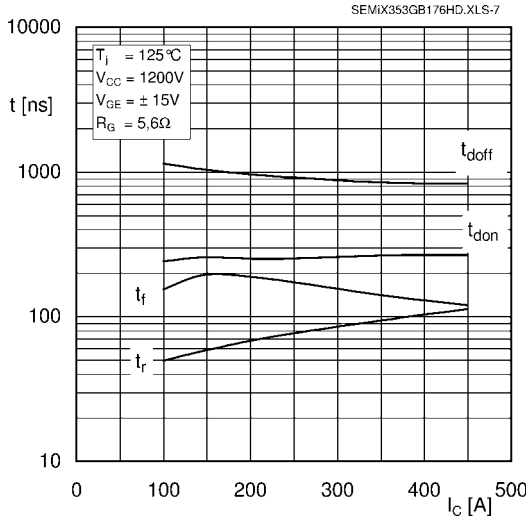


Fig. 7: Typ. switching times vs. I_C

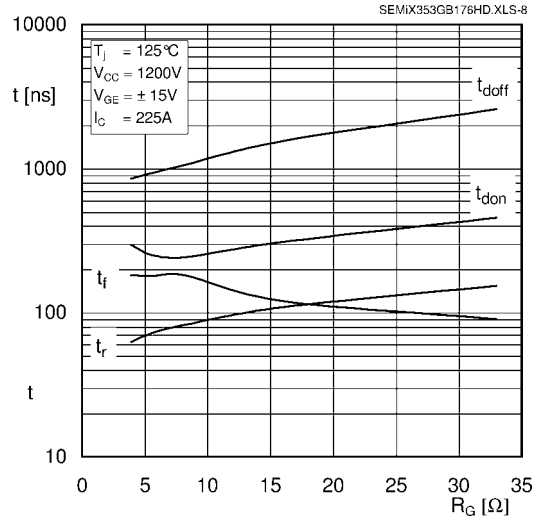


Fig. 8: Typ. switching times vs. gate resistor R_G

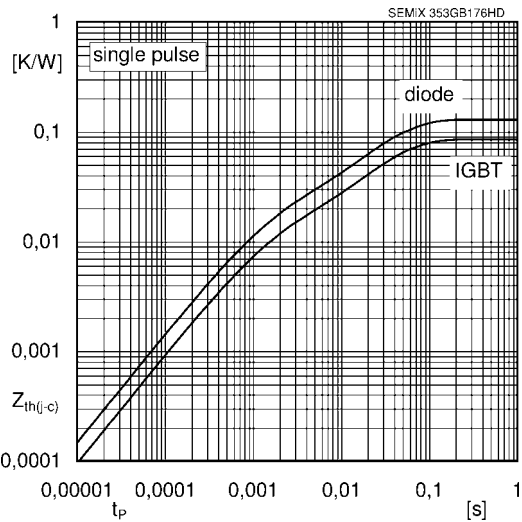


Fig. 9: Typ. transient thermal impedance

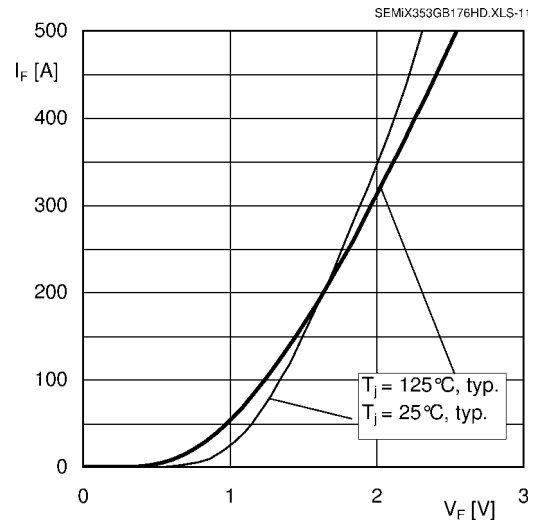


Fig. 10: Typ. CAL diode forward charact., incl. R_{CC+EE}

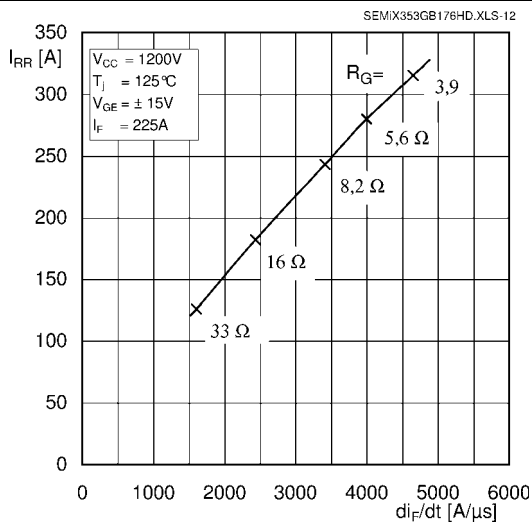


Fig. 11: Typ. CAL diode peak reverse recovery current

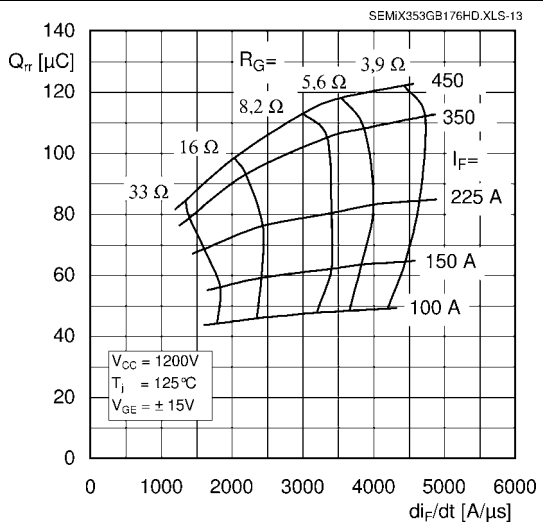


Fig. 12: Typ. CAL diode recovery charge

